AOK60B65M3

650V, 60A Alpha IGBT™

With soft and fast recovery anti-parallel diode

General Description

- Latest AlphaIGBT (α IGBT) technology
- 650V breakdown voltage
- Very fast and soft recovery freewheeling diode
- High efficient turn-on di/dt controllability
- Low VCE(SAT) enables high efficiencies
- Low turn-off switching loss and softness
- Very good EMI behavior
- High short-circuit ruggedness

Applications

- Motor Drives
- Welding Machines
- UPS and Solar Inverters
- Other hard switching applications

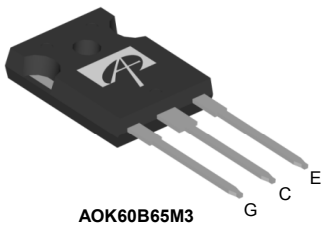
Product Summary

V_{CE}	650V
I_C (T_C=100°C)	60A
$V_{CE(sat)}$ (T_J=25°C)	1.94V

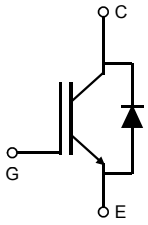
RoHS Compliant

Top View

TO-247



AOK60B65M3



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOK60B65M3	TO247	Tube	240

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	AOK60B65M3	Units
Collector-Emitter Voltage		V_{CE}	650	V
Gate-Emitter Voltage		V_{GE}	±30	V
Continuous Collector Current	T_C=25°C	I_C	120	A
	T_C=100°C		60	
Pulsed Collector Current, Limited by T_{Jmax}		I_{CM}	180	A
Turn off SOA, $V_{CE} \leqslant$ 650V, Limited by T_{Jmax}		I_{LM}	180	A
Continuous Diode Forward Current	T_C=25°C	I_F	60	A
	T_C=100°C		30	
Diode Pulsed Current, Limited by T_{Jmax}		I_{FM}	180	A
Short circuit withstanding time [1] V_{GE} = 15V, $V_{CC} \leqslant$ 400V, $T_J \leqslant$ 175°C		t_{SC}	5	µs
Power Dissipation	T_C=25°C	P_D	500	W
	T_C=100°C		250	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		T_L	300	°C

Thermal Characteristics

Parameter	Symbol	AOK60B65M3	Units
Maximum Junction-to-Ambient	$R_{\theta JA}$	40	°C/W
Maximum IGBT Junction-to-Case	$R_{\theta JC}$	0.3	°C/W
Maximum Diode Junction-to-Case	$R_{\theta JC}$	1	°C/W

1) Allowed number of short circuits: <1000; time between short circuits: >1s.

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{CES}	Collector-Emitter Breakdown Voltage	I_C=1mA, V_{GE}=0V, T_J=25°C		650	-	-	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V_{GE}=15V, I_C=60A	T_J=25°C	-	1.94	2.45	V
			T_J=125°C	-	2.35	-	
			T_J=175°C	-	2.6	-	
V_F	Diode Forward Voltage	V_{GE}=0V, I_C=60A	T_J=25°C	-	1.91	2.4	V
			T_J=125°C	-	2.15	-	
			T_J=175°C	-	2.1	-	
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	V_{CE}=5V, I_C=1mA		-	4.8	-	V
I_{CES}	Zero Gate Voltage Collector Current	V_{CE}=650V, V_{GE}=0V	T_J=25°C	-	-	10	µA
			T_J=125°C	-	-	1000	
			T_J=175°C	-	-	15000	
I_{GES}	Gate-Emitter leakage current	V_{CE}=0V, V_{GE}=±30V		-	-	±100	nA
g_{FS}	Forward Transconductance	V_{CE}=20V, I_C=60A		-	35	-	S
DYNAMIC PARAMETERS							
C_{ies}	Input Capacitance	V_{GE}=0V, V_{CC}=25V, f=1MHz		-	2800	-	pF
C_{oes}	Output Capacitance			-	330	-	pF
C_{res}	Reverse Transfer Capacitance			-	118	-	pF
Q_g	Total Gate Charge	V_{GE}=15V, V_{CC}=520V, I_C=60A		-	106	-	nC
Q_{ge}	Gate to Emitter Charge			-	35	-	nC
Q_{gc}	Gate to Collector Charge			-	41	-	nC
$I_{C(SC)}$	Short circuit collector current	V_{GE}=15V, V_{CC}=400V, $t_{sc}\leqslant$5us, $T_J\leqslant$175°C		-	222	-	A
R_g	Gate resistance	V_{GE}=0V, V_{CC}=0V, f=1MHz		-	14	-	Ω
SWITCHING PARAMETERS, (Load Inductive, T_J=25°C)							
$t_{D(on)}$	Turn-On DelayTime	T_J=25°C V_{GE}=15V, V_{CC}=400V, I_C=60A, R_G=5Ω		-	44	-	ns
t_r	Turn-On Rise Time			-	84	-	ns
$t_{D(off)}$	Turn-Off Delay Time			-	166	-	ns
t_f	Turn-Off Fall Time			-	75	-	ns
E_{on}	Turn-On Energy			-	2.6	-	mJ
E_{off}	Turn-Off Energy			-	1.3	-	mJ
E_{total}	Total Switching Energy			-	3.9	-	mJ
t_{rr}	Diode Reverse Recovery Time	T_J=25°C I_F=60A,dI/dt=200A/µs,V_{CC}=400V		-	346	-	ns
Q_{rr}	Diode Reverse Recovery Charge			-	1.3	-	µC
I_{rm}	Diode Peak Reverse Recovery Current			-	7.5	-	A
SWITCHING PARAMETERS, (Load Inductive, T_J=175°C)							
$t_{D(on)}$	Turn-On DelayTime	T_J=175°C V_{GE}=15V, V_{CC}=400V, I_C=60A, R_G=5Ω		-	42	-	ns
t_r	Turn-On Rise Time			-	83	-	ns
$t_{D(off)}$	Turn-Off Delay Time			-	208	-	ns
t_f	Turn-Off Fall Time			-	77	-	ns
E_{on}	Turn-On Energy			-	2.9	-	mJ
E_{off}	Turn-Off Energy			-	1.9	-	mJ
E_{total}	Total Switching Energy			-	4.8	-	mJ
t_{rr}	Diode Reverse Recovery Time	T_J=175°C I_F=60A,dI/dt=200A/µs,V_{CC}=400V		-	557	-	ns
Q_{rr}	Diode Reverse Recovery Charge			-	3.1	-	µC
I_{rm}	Diode Peak Reverse Recovery Current			-	11	-	A

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

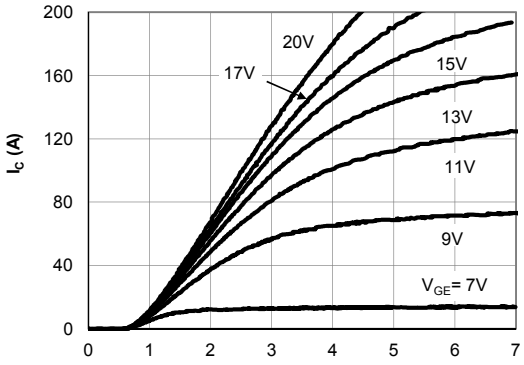


Fig 1: Output Characteristic (T_j=25°C)

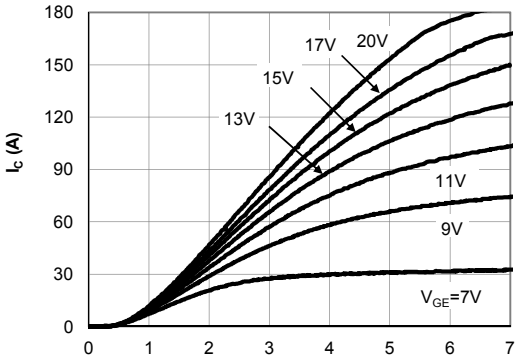


Fig 2: Output Characteristic (T_j=175°C)

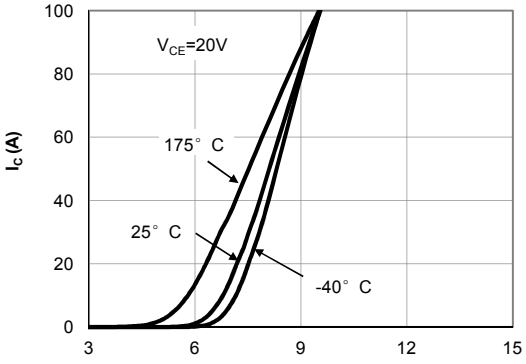


Fig 3: Transfer Characteristic

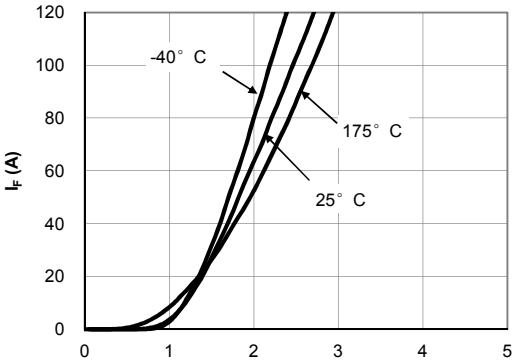


Fig 4: Diode Characteristic

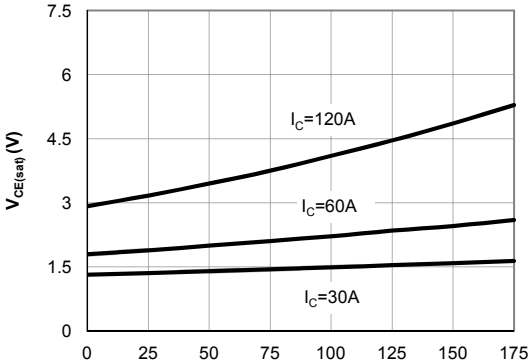


Fig 5: Collector-Emitter Saturation Voltage vs. Junction Temperature

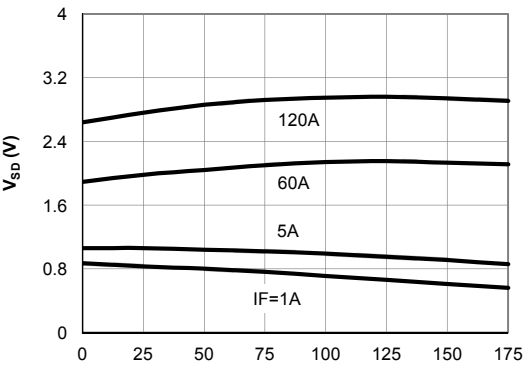


Fig 6: Diode Forward voltage vs. Junction Temperature

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

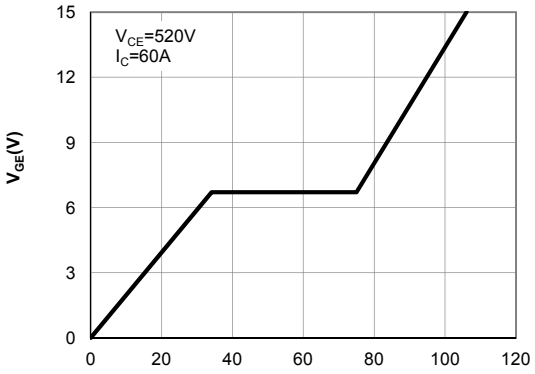


Fig 7: Gate-Charge Characteristics

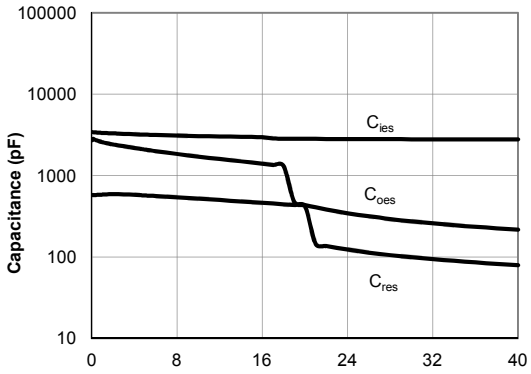


Fig 8: Capacitance Characteristic

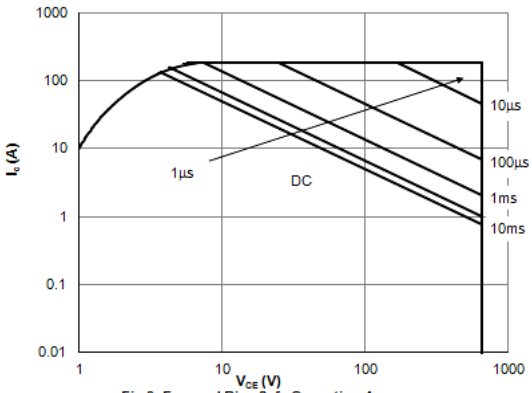


Fig 9: Forward Bias Safe Operating Area
(T_C=25°C,V_{GE}=15V)

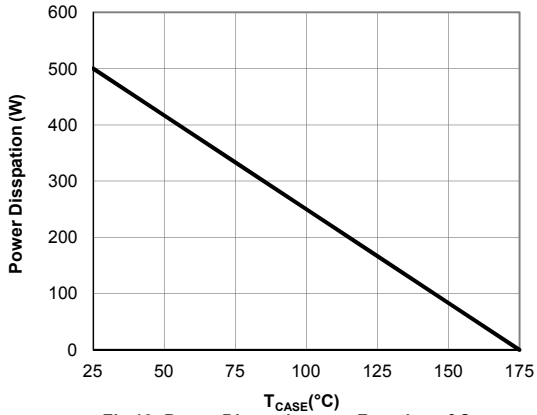


Fig 10: Power Disspation as a Function of Case

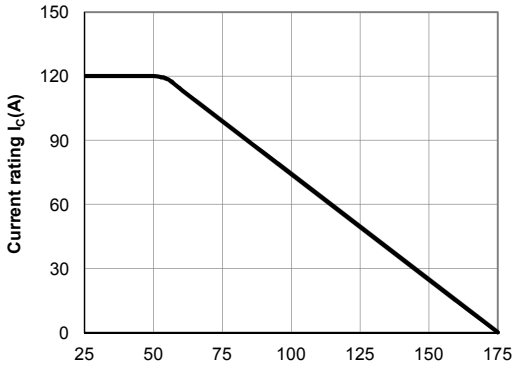


Fig 11: Current De-rating

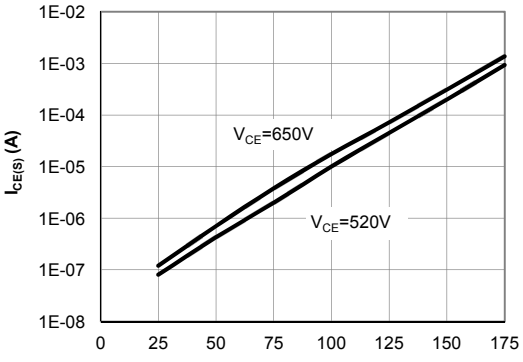


Fig 12: Diode Reverse Leakage Current vs. Junction Temperature

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

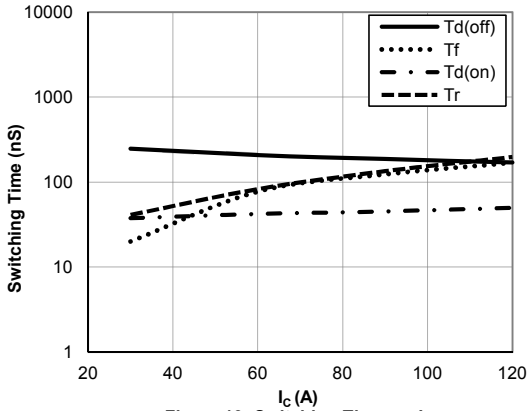


Figure 13: Switching Time vs. I_C
(T_j=175°C,V_{GE}=15V,V_{CE}=400V,R_g=5Ω)

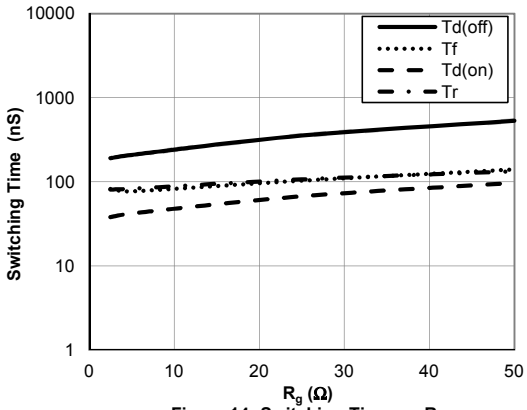


Figure 14: Switching Time vs. R_g
(T_j=175°C,V_{GE}=15V,V_{CE}=400V,I_C=60A)

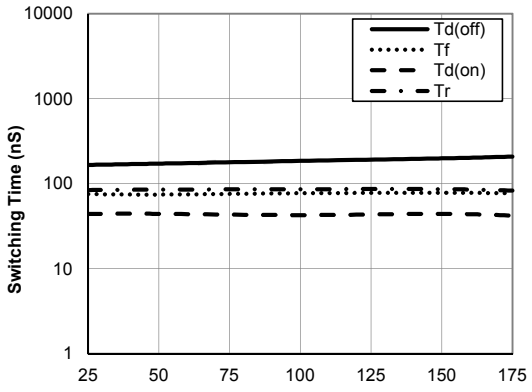


Figure 15: Switching Time vs.T_j
(V_{GE}=15V,V_{CE}=400V,I_C=60A,R_g=5Ω)

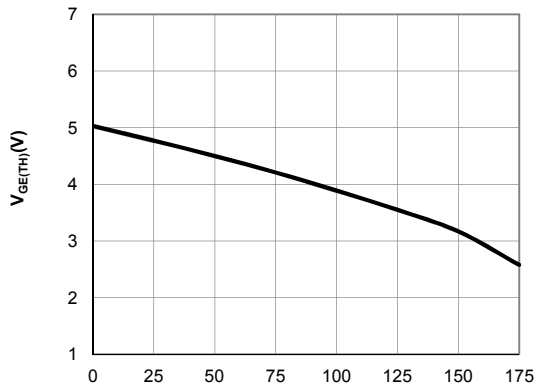


Figure 16: $V_{GE(TH)}$ vs. T_j

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

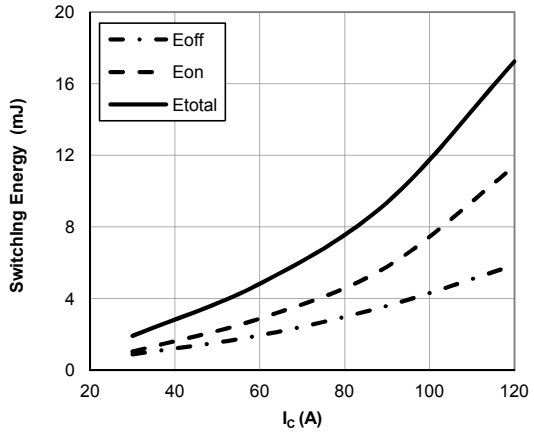


Figure 17: Switching Loss vs. I_C
(T_j=175°C,V_{GE}=15V,V_{CE}=400V,R_g=5Ω)

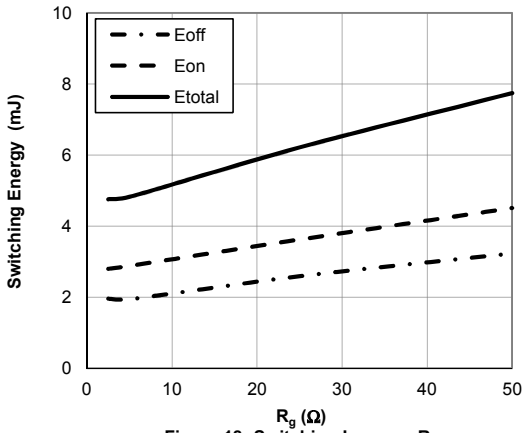


Figure 18: Switching Loss vs. R_g
(T_j=175°C,V_{GE}=15V,V_{CE}=400V,I_C=60A)

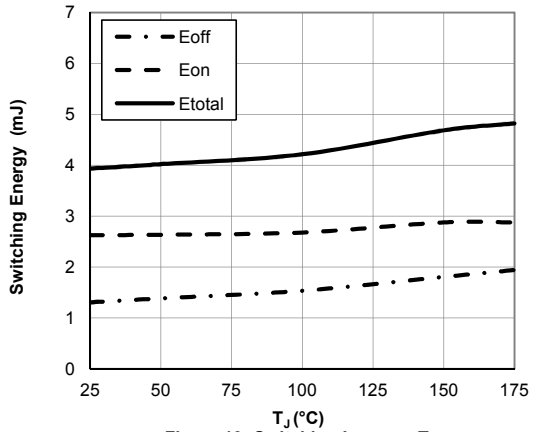


Figure 19: Switching Loss vs. T_j
(V_{GE}=15V,V_{CE}=400V,I_C=60A,R_g=5Ω)

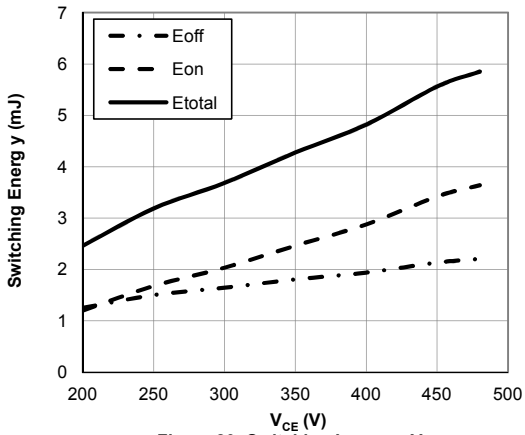


Figure 20: Switching Loss vs. V_{CE}
(T_j=175°C,V_{GE}=15V,I_C=60A,R_g=5Ω)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

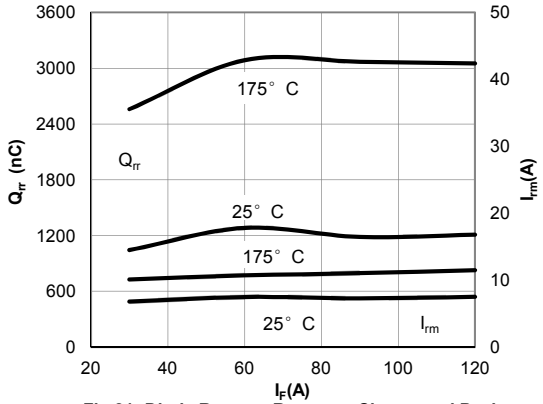


Fig 21: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current (V_{GE}=15V,V_{CE}=400V, di/dt=200A/µs)

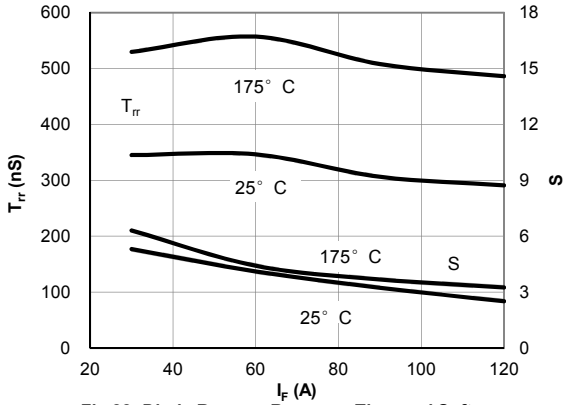


Fig 22: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current (V_{GE}=15V,V_{CE}=400V, di/dt=200A/µs)

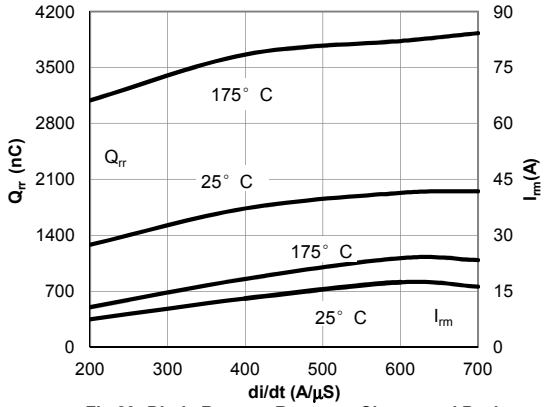


Fig 23: Diode Reverse Recovery Charge and Peak Current vs. di/dt (V_{GE}=15V,V_{CE}=400V,I_F=60A)

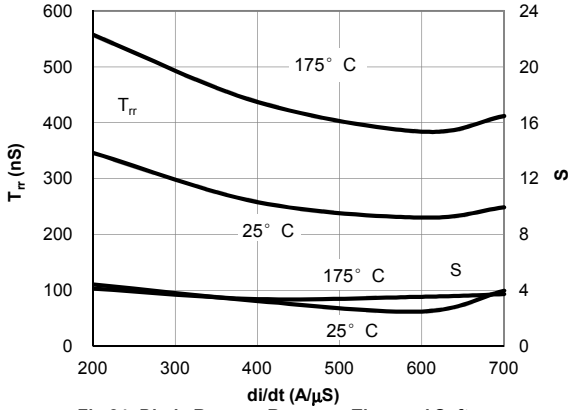


Fig 24: Diode Reverse Recovery Time and Softness Factor vs. di/dt (V_{GE}=15V,V_{CE}=400V,I_F=60A)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

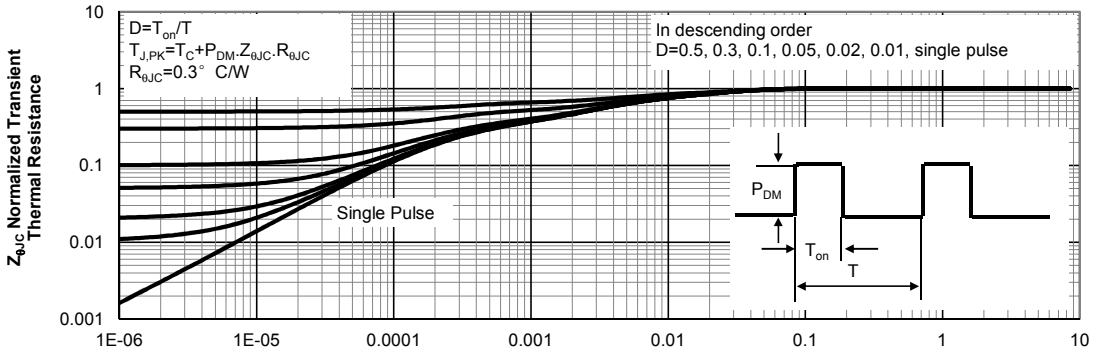


Figure 25: Normalized Maximum Transient Thermal Impedance for IGBT

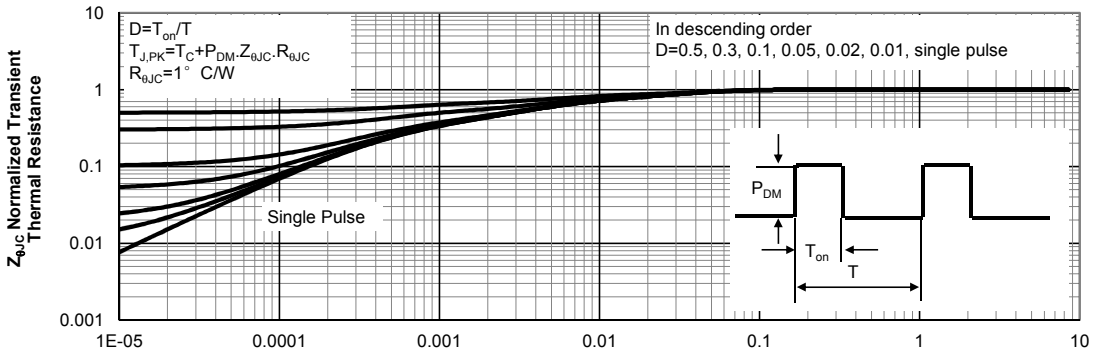
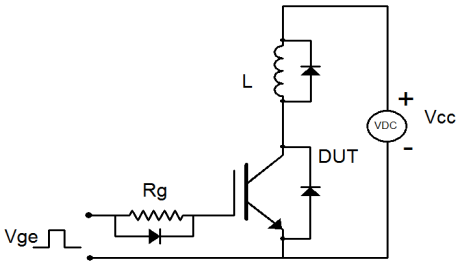
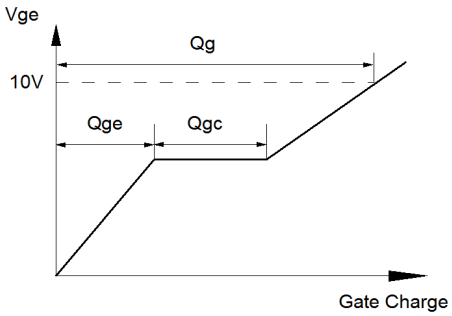


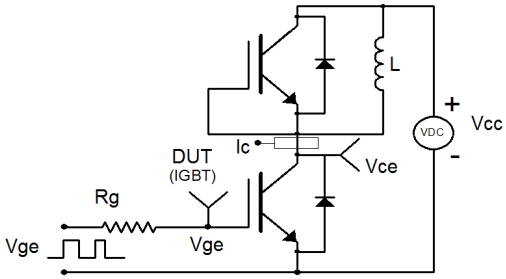
Figure 26: Normalized Maximum Transient Thermal Impedance for Diode

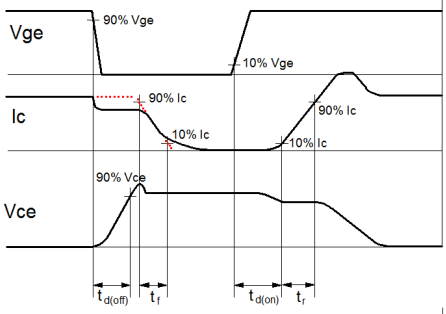
Gate Charge Test Circuit & Waveform

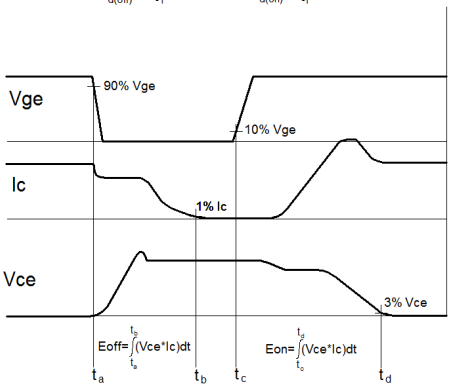




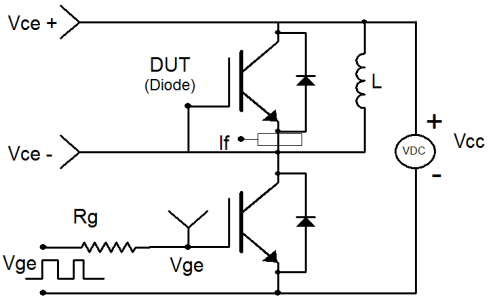
Inductive Switching Test Circuit & Waveforms

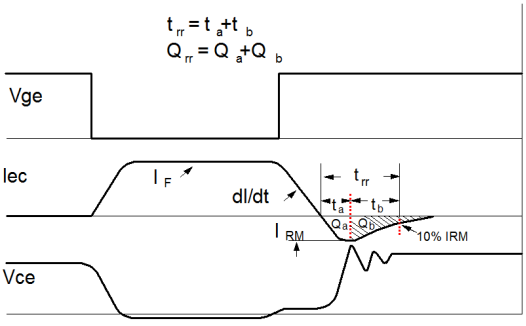






Diode Recovery Test Circuit & Waveforms





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Parça koduyla arama

Üretici parça numarasını yazın; stok ve fiyatı hemen görün.

www.entegreci.com

Ürün kategorileri

Entegreden kapasitöre tüm elektronik komponent kategorileri.

Kategorilere göz atın

Üreticiler

Aradığınız üreticinin ürünlerini tek sayfada inceleyin.

Üreticileri görün

Toplu alım ve teklif

Listede olmayan ya da yüksek adetli parçalar için teklif isteyin.

Teklif isteyin

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